DATA SHEET

BIPOLAR ANALOG INTEGRATED CIRCUITS μ PC2747TB, μ PC2748TB

3 V, SUPER MINIMOLD SILICON MMIC AMPLIFIER FOR MOBILE COMMUNICATIONS

DESCRIPTION

NEC

The μ PC2747TB, μ PC2748TB are silicon monolithic integrated circuits designed as amplifier for mobile communications. These ICs are packaged in super minimold package which is smaller than conventional minimold.

These ICs are manufactured using our 20 GHz fr NESAT III silicon bipolar process. This process uses silicon nitride passivation film and gold electrodes. These materials can protect chip surface from external pollution and prevent corrosion/migration. Thus, these ICs have excellent performance, uniformity and reliability.

FEATURES

•	Supply voltage	: Vcc = 2.7 to 3.3 V
•	Noise figure	: µPC2747TB ; NF = 3.3 dB TYP. @ f = 900 MHz
		μPC2748TB ; NF = 2.8 dB TYP. @ f = 900 MHz
•	Power gain	: μ PC2747TB ; G _P = 12 dB TYP. @ f = 900 MHz
		μ PC2748TB ; G _P = 19 dB TYP. @ f = 900 MHz
•	Operating frequency	: μPC2747TB ; DC to 1.8 GHz
		μPC2748TB ; 0.2 to 1.5 GHz
•	Isolation	: µPC2747TB ; ISL = 40 dB TYP. @ f = 900 MHz
		μPC2748TB ; ISL = 40 dB TYP. @ f = 900 MHz
•	High-density surface mounting	: 6-pin super minimold package ($2.0 \times 1.25 \times 0.9$ mm)

APPLICATION

• Buffer amplifiers for mobile telephones, etc. (PDC800M, GSM)

ORDERING INFORMATION

Part Number	Package	Marking	Supplying Form
μPC2747TB-E3	6-pin super minimold	C1S	Embossed tape 8 mm wide
μPC2748TB-E3		C1T	1, 2, 3 pins face the perforation side of the tapeQty 3 kpcs/reel

Remark To order evaluation samples, contact your nearby sales office. Part number for sample order: μ PC2747TB, μ PC2748TB

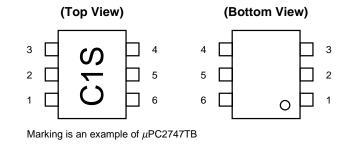
Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version. Not all devices/types available in every country. Please check with local NEC Compound Semiconductor Devices representative for availability and additional information.

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The mark **★** shows major revised points.

PIN CONNECTIONS



Pin No.	Pin Name	
1	INPUT	
2	GND	
3	GND	
4	OUTPUT	
5	GND	
6	Vcc	

PRODUCT LINE-UP (TA = +25°C, Vcc = 3.0 V, Zs = ZL =50 Ω)

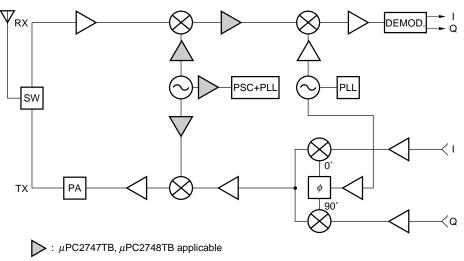
Part No.	f _u (GHz)	Po _(sat) (dBm)	G⊦ (dB)	NF (dB)	lcc (mA)	Package	Marking
μPC2745T	2.7	-1.0	12	6.0	7.5	6-pin minimold	C1Q
μPC2745TB						6-pin super minimold	
μPC2746T	1.5	0	19	4.0	7.5	6-pin minimold	C1R
μPC2746TB						6-pin super minimold	
μPC2747T	1.8	-7.0	12	3.3	5.0	6-pin minimold	C1S
μPC2747TB						6-pin super minimold	
μPC2748T	1.5	-3.5	19	2.8	6.0	6-pin minimold	C1T
μPC2748TB						6-pin super minimold	
μPC2749T	2.9	-6.0	16	4.0	6.0	6-pin minimold	C1U
μPC2749TB						6-pin super minimold	

Remark Typical performance. Please refer to ELECTRICAL CHARACTERISTICS in detail.

Caution The package size distinguishes between minimold and super minimold.

SYSTEM APPLICATION EXAMPLE





PIN EXPLANATION

Pin No.	Pin Name	Applied Voltage (V)	Pin Voltage (V) ^{Note}	Function and Applications	Internal Equivalent Circuit
1	INPUT	-	0.80 0.80	Signal input pin. A internal matching circuit, configured with resistors, enables 50Ω connection over a wide band. This pin must be coupled to signal source with capacitor for DC cut.	6
2 3 5	GND	0	_	Ground pin. This pin should be connected to system ground with minimum inductance. Ground pattern on the board should be formed as wide as possible. All the ground pins must be connected together with wide ground pattern to decrease impedance difference.	
4	OUTPUT	-	2.79 2.72	Signal output pin. A internal matching circuit, configured with resistors, enables 50Ω connection over a wide band. This pin must be coupled to next stage with capacitor for DC cut.	3 $2 - 5The above diagram is for the \muPC2747TB.The resistor marked with an asterisk$
6	Vcc	2.7 to 3.3	_	Power supply pin. This pin should be externally equipped with bypass capacity to minimize ground impedance.	does not exist in the μ PC2748TB.

Note Pin voltage is measured at Vcc = 3.0 V. Above: μ PC2747TB, Below: μ PC2748TB

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Conditions	Ratings	Unit
Supply Voltage	Vcc	T _A = +25°C	4.0	V
Circuit Current	Icc	T _A = +25°C	15	mA
Power Dissipation	PD	T _A = +85°C Note	270	mW
Operating Ambient Temperature	TA		-40 to +85	°C
Storage Temperature	Tstg		–55 to +150	°C
Input Power	Pin	T _A = +25°C	0	dBm

Note Mounted on double-sided copper-clad 50 \times 50 \times 1.6 mm epoxy glass PWB

RECOMMENDED OPERATING RENGE

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage	Vcc	2.7	3.0	3.3	V

ELECTRICAL CHARACTERISTICS

(TA = +25°C, Vcc = 3.0 V, Zs = ZL = 50 Ω , unless otherwise specified)

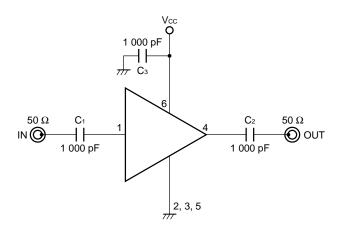
Parameter	Symbol	Test Conditions	μF	μPC2747TB		μPC2748TB			Unit
			MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Circuit Current	Icc	No Signal	3.8	5.0	7.0	4.5	6.0	8.0	mA
Power Gain	Gp	f = 900 MHz	9	12	14	16	19	21	dB
Noise Figure	NF	f = 900 MHz	-	3.3	4.5	-	2.8	4.0	dB
Upper Limit Operating Frequency	fu	3 dB down below from gain at f = 0.9 GHz	1.5	1.8	-	1.2	1.5	-	GHz
Lower Limit Operating Frequency	f∟	3 dB down below from gain at f = 0.9 GHz	-	-	-	-	0.2	0.4	GHz
Isolation	ISL	f = 900 MHz	35	40	-	35	40	_	dB
Input Return Loss	RLin	f = 900 MHz	11	14	-	8.5	11.5	-	dB
Output Return Loss	RLout	f = 900 MHz	7	10	-	5.5	8.5	_	dB
Saturated Output Power	Po (sat)	$f = 900 \text{ MHz}, P_{in} = -8 \text{ dBm}$	-9.5	-7.0	-	-6.0	-3.5	-	dBm

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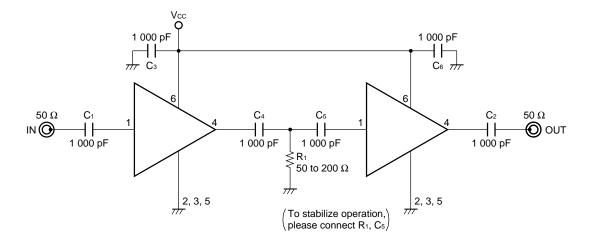
Parameter	Symbol	Test Conditions	Refe	Reference	
			μPC2747TB	μPC2748TB	
Circuit Current	Icc	Vcc = 1.8 V, No signal	3.0	3.5	mA
Power Gain	G₽	Vcc = 1.8 V, f = 900 MHz	5.5	11.5	dB
Noise Figure	NF	Vcc = 1.8 V, f = 900 MHz	5.2	4.5	dB
Upper Limit Operating Frequency	fu	Vcc = 1.8 V, 3 dB down below from gain at f = 0.9 GHz	1.8	1.5	GHz
Lower Limit Operating Frequency	f∟	Vcc = 1.8 V, 3 dB down below from gain at f = 0.9 GHz	_	0.2	GHz
Isolation	ISL	Vcc = 1.8 V, f = 900 MHz	34	34	dB
Input Return Loss	RLin	Vcc = 1.8 V, f = 900 MHz	11	10	dB
Output Return Loss	RLout	Vcc = 1.8 V, f = 900 MHz	13	12	dB
Saturated Output Power	Po (sat)	$V_{CC} = 1.8 \text{ V}, \text{ f} = 900 \text{ MHz}, \text{ P}_{\text{in}} = -8 \text{ dBm}$	-13.7	-10.0	dBm
3rd Order Intermodulation Distortion	IМз	$V_{cc} = 3.0 V, P_{out} = -20 dBm,$ f1 = 900 MHz, f2 = 902 MHz	-34	-38	dBc
		Vcc = 1.8 V, Pout = -20 dBm, f1 = 900 MHz, f2 = 902 MHz	-20	-28	

STANDARD CHARACTERISTICS FOR REFERENCE (TA = +25°C, Zs = ZL =50 Ω)

TEST CIRCUIT



EXAMPLE OF APPLICATION CIRCUIT



The application circuits and their parameters are for reference only and are not intended for use in actual design-ins.

CAPACITORS FOR Vcc, INPUT AND OUTPUT PINS

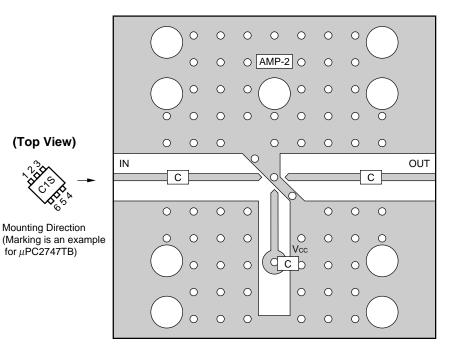
1 000 pF capacitors are recommendable as bypass capacitor for Vcc pin and coupling capacitors for input/output pins.

Bypass capacitor for Vcc pin is intended to minimize Vcc pin's ground impedance. Therefore, stable bias can be supplied against Vcc fluctuation.

Coupling capacitors for input/output pins are intended to minimize RF serial impedance and cut DC.

To get flat gain from 100 MHz up, 1 000 pF capacitors are assembled on the test circuit. [Actually, 1 000 pF capacitors give flat gain at least 10 MHz. In the case of under 10 MHz operation, increase the value of coupling capacitor such as 2 200 pF. Because the coupling capacitors are determined by the equation of $fc = 1/(2 \pi RC)$.]

ILLUSTRATION OF THE TEST CIRCUIT ASSEMBLED ON EVALUATION BOARD



COMPONENT LIST

	Value
С	1 000 pF

Notes

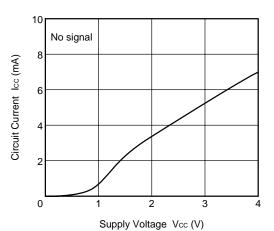
- 1. $30 \times 30 \times 0.4$ mm double-sided copper-clad polyimide board.
- 2. Back side: GND pattern
- 3. Solder plated on pattern
- **4.** \circ \bigcirc : Through holes

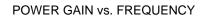
For more information on the use of this IC, refer to the following application note: USAGE AND APPLICATIONS OF 6-PIN MINI-MOLD, 6-PIN SUPER MINI-MOLD SILICON HIGH-FREQUENCY WIDEBAND AMPLIFIER MMIC (P11976E).

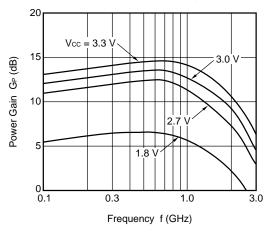
★ TYPICAL CHARACTERISTICS (T_A = +25°C, unless otherwise specified)

– μPC2747TB –

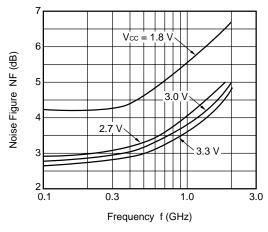
CIRCUIT CURRENT vs. SUPPLY VOLTAGE

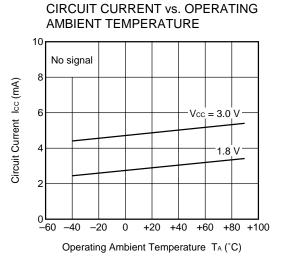




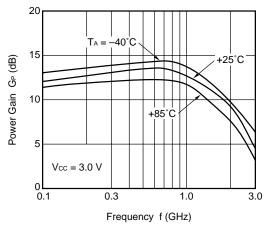


NOISE FIGURE vs. FREQUENCY

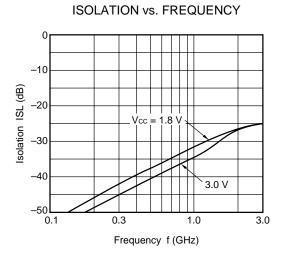




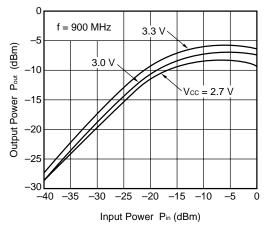
POWER GAIN vs. FREQUENCY

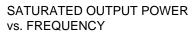


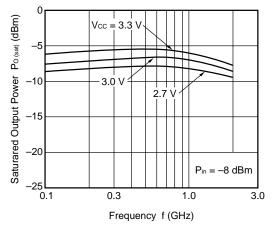
– μPC2747TB –



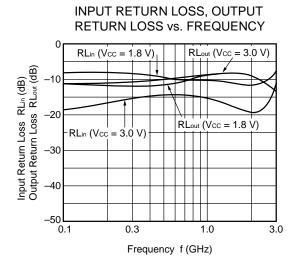
OUTPUT POWER vs. INPUT POWER



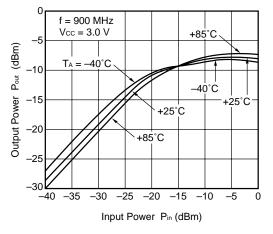




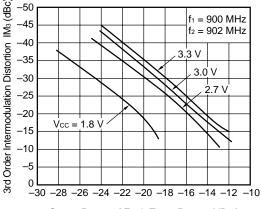
Remark The graphs indicate nominal characteristics.



OUTPUT POWER vs. INPUT POWER



3RD ORDER INTERMODULATION DISTORTION vs. OUTPUT POWER OF EACH TONE

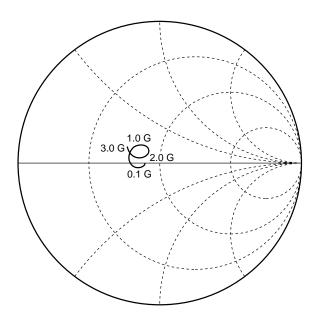


Output Power of Each Tone Po (each) (dBm)

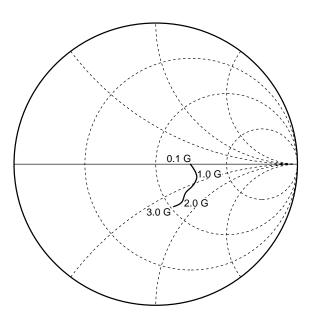
SMITH CHART (TA = +25°C, Vcc = 3.0 V)

– μPC2747TB –

S11-FREQUENCY



S22-FREQUENCY



S-PARAMETERS

– μPC2747TB –

S-parameters/Noise parameters are provided on the NEC Compound Semiconductor Devices Web site in a form (S2P) that enables direct import to a microwave circuit simulator without keyboard input.

Click here to download S-parameters.

 $[\text{RF and Microwave}] \rightarrow [\text{Device Parameters}]$

URL http://www.csd-nec.com/

CIRCUIT CURRENT vs. OPERATING

AMBIENT TEMPERATURE

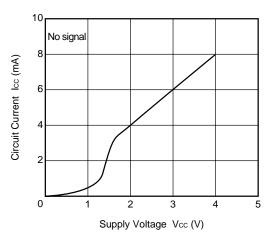
10

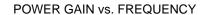
No signal

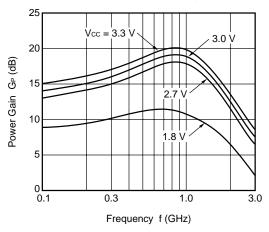
TYPICAL CHARACTERISTICS (TA = +25°C, unless otherwise specified)

- μPC2748TB -

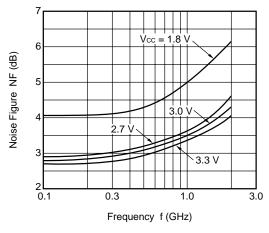
CIRCUIT CURRENT vs. SUPPLY VOLTAGE



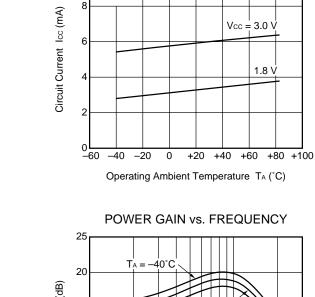


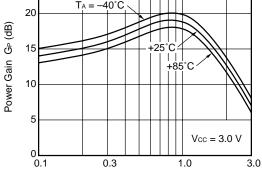


NOISE FIGURE vs. FREQUENCY



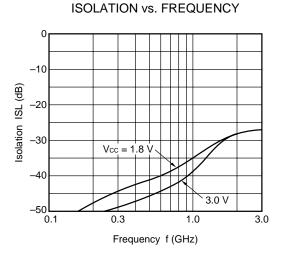




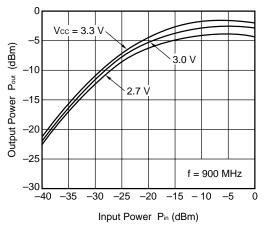


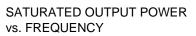


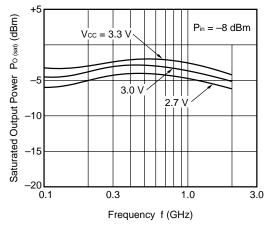
– μPC2748TB –



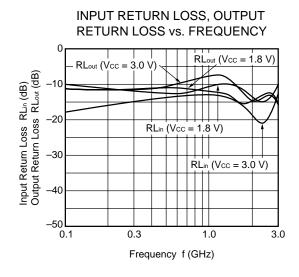
OUTPUT POWER vs. INPUT POWER



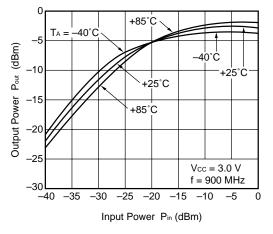




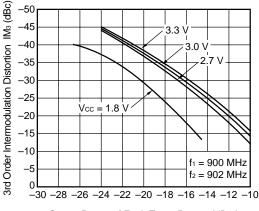
Remark The graphs indicate nominal characteristics.



OUTPUT POWER vs. INPUT POWER



3RD ORDER INTERMODULATION DISTORTION vs. OUTPUT POWER OF EACH TONE

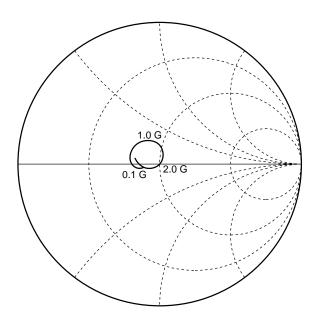


Output Power of Each Tone Po (each) (dBm)

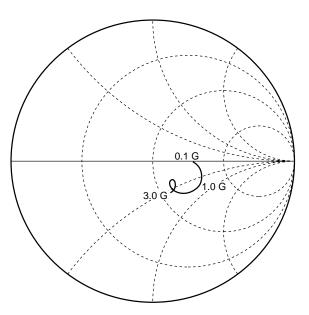
SMITH CHART (TA = +25°C, Vcc = 3.0 V)

– μPC2748TB –

S11-FREQUENCY



S22-FREQUENCY



S-PARAMETERS

– μPC2748TB –

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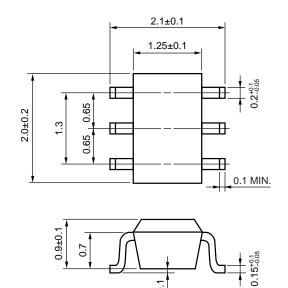
Click here to download S-parameters.

 $[\text{RF and Microwave}] \rightarrow [\text{Device Parameters}]$

URL http://www.csd-nec.com/

PACKAGE DIMENSIONS

6-PIN SUPER MINIMOLD (UNIT: mm)



0 to 0.1

NOTES ON CORRECT USE

- (1) Observe precautions for handling because of electro-static sensitive devices.
- (2) Form a ground pattern as widely as possible to minimize ground impedance (to prevent undesired oscillation).
 All the ground pins must be connected together with wide ground pattern to decrease impedance difference.
- (3) The bypass capacitor should be attached to Vcc line.
- (4) The DC cut capacitor must be attached to input and output pin.

★ RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions		Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature) Time at peak temperature Time at temperature of 220°C or higher Preheating time at 120 to 180°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 60 seconds or less : 120±30 seconds : 3 times : 0.2%(Wt.) or below	IR260
VPS	Peak temperature (package surface temperature) Time at temperature of 200°C or higher Preheating time at 120 to 150°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 215°C or below : 25 to 40 seconds : 30 to 60 seconds : 3 times : 0.2%(Wt.) or below	VP215
Wave Soldering	Peak temperature (molten solder temperature) Time at peak temperature Preheating temperature (package surface temperature) Maximum number of flow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 120°C or below : 1 time : 0.2%(Wt.) or below	WS260
Partial Heating	Peak temperature (pin temperature) Soldering time (per side of device) Maximum chlorine content of rosin flux (% mass)	: 350°C or below : 3 seconds or less : 0.2%(Wt.) or below	HS350

Caution Do not use different soldering methods together (except for partial heating).

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M8E 00.4-0110

▶ Business issue

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► Technical issue

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